

IR HL YS 7 9 7 0 3 4 C M - SCS A 00

TRANSISTOR TYPE

- H – Radiation Hardened HEXFET
- HL – RadHard Logic Level MOSFET
- HS – RadHard Synchronous Rectifier
- HSL – RadHard Sync. Rectifier (low inductance)

PACKAGE DESIGNATOR

All packages have metal lids unless otherwise noted

- Blank – TO-204AA, AE (TO-3)
- C – Chip / Die (no package)
- W – Wafer (no package)
- E – (U) LCC-18
- F – (T2) TO-205AF (TO-39, low profile)
- G – (M1) MO-036AB (14 lead ceramic DIP)
- I – TO-259AA
- M – (T1) TO-254AA
- MA – TO-254AA tabless
- MB – (D4) TO-254AA tabless, low ohmic
- MG – TO-254AA, surface mount lead formed
- MJ – TO-254AA tabless, surface mount lead formed
- MK – TO-254AA tabless, low ohmic, surface mount lead formed – at surface plane
- ML – (D1) TO-254AA tabless, low ohmic, surface mount lead formed – below surface plane
- MS – (T1) TO-254AA low ohmic
- N – (U1) SMD-1
- NA – (U2) SMD-2
- NJ – (U3) SMD-0.5, metal lid
- NJC – SMD-0.5, ceramic lid
- NKC – SMD-0.5, ceramic lid, high-voltage
- NM – (U8) SMD-0.2, metal lid
- NMC – SMD-0.2, ceramic lid
- NPC – SMD-0.1, ceramic lid
- NS – (U2A) SuplR-SMD™
- PB – Power Block, isolated
- Q – LCC-28 (quad die)
- UB – (UB) LCC-3, metal lid, shielded - tied to 4th pin
- UBC – LCC-3, ceramic lid, shielded
- UBCN – LCC-3, ceramic lid, isolated
- UBN – LCC-3, metal lid, isolated
- UC – (UC) LCC-6
- V – (T8) TO-258AA
- Y – (T3) TO-257AA
- YA – TO-257AA tabless
- YB – (D5) TO-257AA tabless, low ohmic
- YJ – (D3) TO-257AA tabless, surface mount lead formed
- YK – TO-257AA tabless, low ohmic, surface mount lead formed
- YS – TO-257AA low ohmic

TECHNOLOGY

- | | |
|-----------------|--------------------|
| Blank – Gen 4 | 7 – R7 |
| 5 – R5 | 7S – R7, S-line |
| 5S – R5, S-line | 8 – R8 |
| 6 – R6 | 9A – R9 |
| 6S – R6, S-line | CS – CoolMOS Space |

CHANNEL

- Blank – N-Channel
- 6 – mixed N and P Channel
- 9 – P-Channel

SPECIAL SUFFIX (see bottom)

LEAD OPTION

- A – Lead form down on TO-25x (if package is SMD, then lead attached)
- B – Lead form up on TO-25x (if package is SMD, then lead attached and formed)
- C – Lead trimmed
- D – On DBC carrier, applies only to SMD-1 and SMD-2

SCREENING LEVEL

- Blank – no screening
- IR HiRel controlled drawing, die level**
- CDV – 100% visual screening
- CDH – H level
- CDK – K level
- IR HiRel qualified lot, packaged level**
- SCX – TX level, equivalent
- SCV – TXV level, equivalent
- SCS – S level, equivalent

PROCESS VARIATION

- SE – Single Event Effect tolerant

PINOUT

(applies only to TO-257AA package)

- | | |
|----------------|----------------|
| Blank | M |
| Pin1 – Gate | Pin 1 – Drain |
| Pin 2 – Drain | Pin 2 – Source |
| Pin 3 – Source | Pin 3 – Gate |

PACKAGE VARIATION

- Blank – glass eyelet (TO-257AA)
- C – ceramic eyelet (TO-257AA)
- L – long lead (TO-39)

VOLTAGE ADDER

- 0 – full spec rating (does not apply to 60V devices)
- 3 – 30 Volts, e.g. 1x3 is 130 Volts
- 4 – 50 Volts, e.g. 2x4 is 250 Volts or, 0x4 is 60 Volts

DIE SIZE

- 1 – die size 1
- 2 – die size 1.7 & 2
- 3 – die size 3
- 4 – die size 4
- 5 – die size 5
- 6 – die size 6
- A – die size 10
- Z – smallest size

VOLTAGE

- 0 – 60 Volts
- 1 – 100 Volts (or 130V or 150V with voltage adder)
- 2 – 200 Volts (or 250V with voltage adder)
- 3 – 400 Volts
- 4 – 500 Volts (or 550V with voltage adder)
- C – 600 Volts
- Y – 20 Volts
- Z – 30 Volts

TOTAL DOSE HARDNESS

- Blank – 100 krad(Si) "R" P-Channel (G4 only)
- 3 – 300 krad(Si) "F"
- 4 – 600 krad(Si)
- 5 – 500 krad(Si) "G"
- 7 – 100 krad(Si) "R"
- 8 – 1000 krad(Si) "H"

SPECIAL SUFFIX

- 00 – Gold Finish – no solder dip
- 01 – CSI, customer source inspection
- 02 – Gold Finish & CSI
- 03 – DPA
- 04 – DPA & Gold Finish
- 05 – DPA & Gold Finish & CSI
- 06 – X-Ray
- 07 – X-Ray & Gold Finish
- 08 – X-Ray & Gold Finish & CSI
- 09 – X-Ray & CSI

